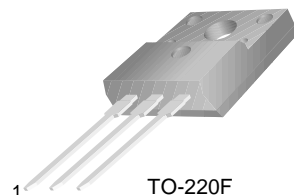


KSC5338F

KSC5338F

High Voltage Power Switch Switching Application

- High Speed Switching
- Wide SOA



TO-220F
1.Base 2.Collector 3.Emitter

NPN Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------|--|------------|------------------|
| V_{CBO} | Collector-Base Voltage | 1000 | V |
| V_{CEO} | Collector-Emitter Voltage | 450 | V |
| V_{EBO} | Emitter-Base Voltage | 9 | V |
| I_C | Collector Current (DC) | 5 | A |
| I_{CP} | Collector Current (Pulse) | 10 | A |
| I_B | Base Current (DC) | 2 | A |
| I_{BP} | Base Current (Pulse) | 4 | A |
| P_C | Collector Dissipation ($T_C=25^\circ\text{C}$) | 40 | W |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature | - 65 ~ 150 | $^\circ\text{C}$ |

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Units |
|------------------------|--------------------------------------|--|---------|------|-------------|---------------|
| BV_{CBO} | Collector-Base Breakdown Voltage | $I_C = 1\text{mA}, I_E = 0$ | 1000 | | | V |
| BV_{CEO} | Collector-Emitter Breakdown Voltage | $I_C = 5\text{mA}, I_B = 0$ | 450 | | | V |
| BV_{EBO} | Emitter-Base Breakdown Voltage | $I_C = 1\text{mA}, I_E = 0$ | 9 | | | V |
| I_{CBO} | Collector Cut-off Current | $V_{CB} = 800\text{V}, V_{BE} = 0$ | | | 10 | μA |
| I_{EBO} | Emitter Cut-off Current | $V_{EB} = 9\text{V}, I_C = 0$ | | | 10 | μA |
| h_{FE1} h_{FE2} | * DC Current Gain | $V_{CE} = 5\text{V}, I_C = 0.5\text{A}$ $V_{CE} = 1\text{V}, I_C = 2\text{A}$ | 15 6 | | 30 | |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C = 1\text{A}, I_B = 0.1\text{A}$ $I_C = 2\text{A}, I_B = 0.4\text{A}$ | | 0.55 | 0.8 0.5 | V V |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage | $I_C = 1\text{A}, I_B = 0.1\text{A}$ $I_C = 2\text{A}, I_B = 0.4\text{A}$ | | | 1.1 1.25 | V V |
| C_{ob} | Output Capacitance | $V_{CB} = 10\text{V}, f = 1\text{MHz}$ | | 70 | | pF |
| C_{ib} | Input Capacitance | $V_{EB} = 8\text{V}, I_C = 0, f = 1\text{MHz}$ | | 1000 | | pF |
| f_T | Current Gain Bandwidth Product | $V_{CE} = 10\text{V}, I_C = 0.1\text{A}$ | | 14 | | MHz |
| t_{ON} | Turn ON Time | $V_{CC} = 125\text{V}, I_C = 1\text{A}$ | | | 200 | ns |
| t_{STG} | Storage Time | $I_{B1} = 0.2\text{A}, I_{B2} = -0.2\text{A}$ | | | 2 | μs |
| t_F | Fall Time | $R_L = 125\Omega$ | | | 500 | ns |

* Pulse Test: Pulse Width=5ms, Duty Cycle≤10%

Typical Characteristics

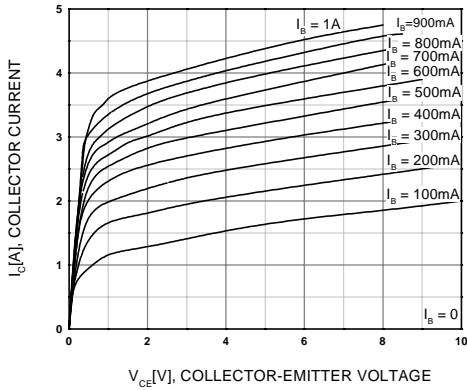


Figure 1. Static Characteristic

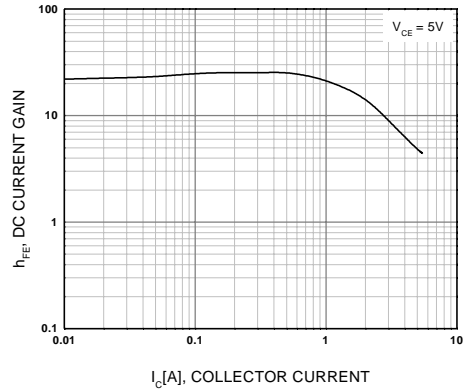


Figure 2. DC current Gain

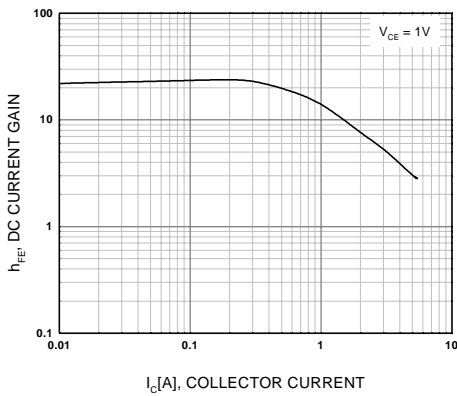


Figure 3. DC current Gain

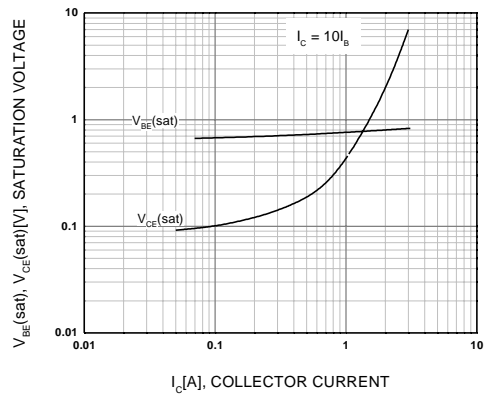


Figure 4. Base-Emitter Saturation Voltage
Collect-Emitter Saturation Voltage

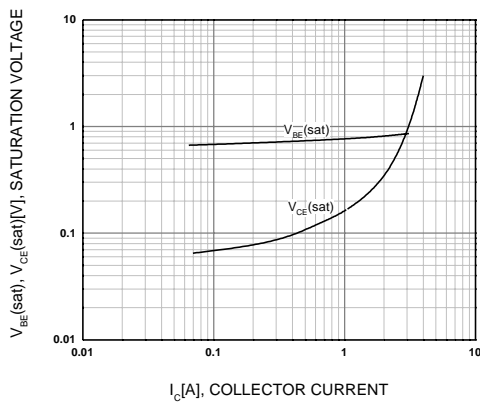


Figure 5. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

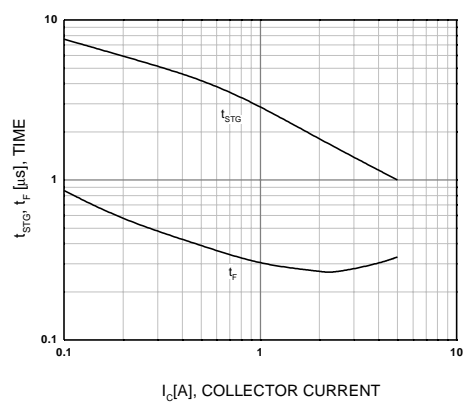


Figure 6. Switching Time

Typical Characteristics (Continued)

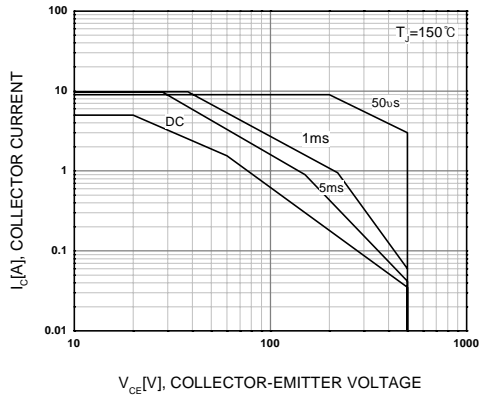


Figure 7. Safe Operating Area

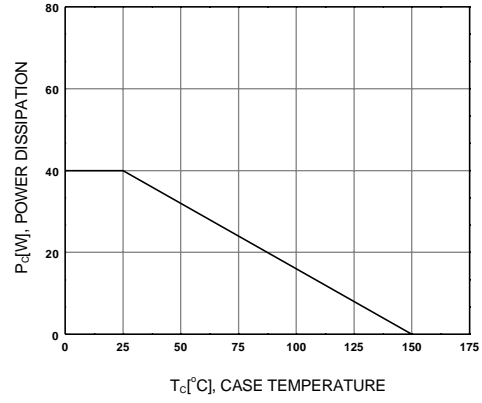
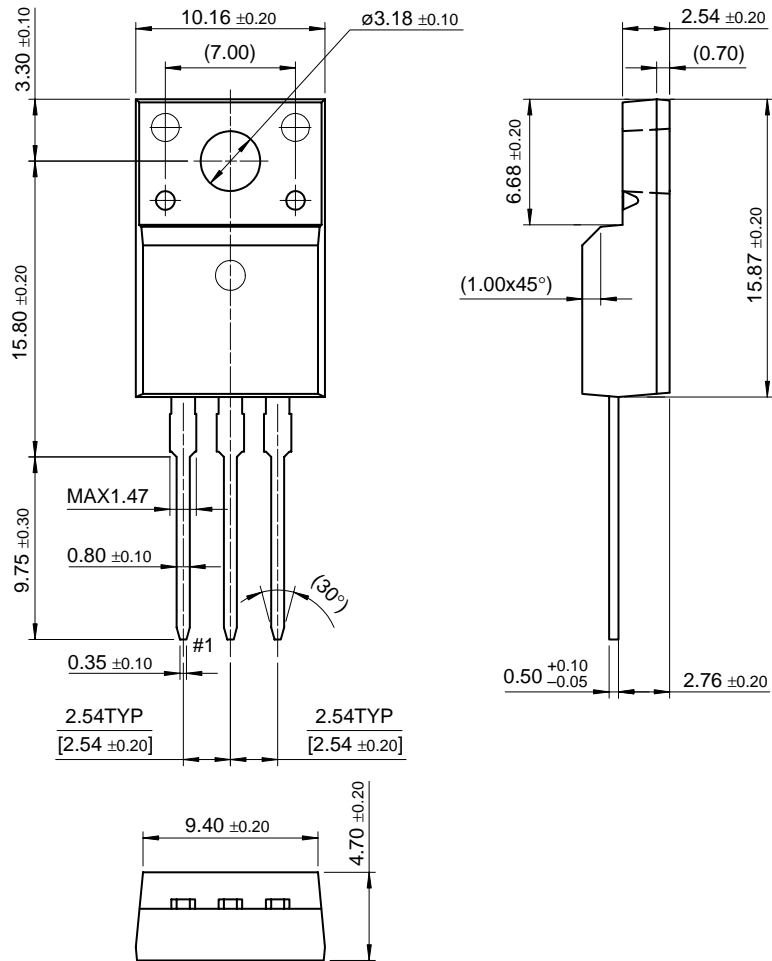


Figure 8. Power Derating

Package Dimensions

KSC5338F

TO-220F



Dimensions in Millimeters

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| CROSSVOLT™ | POP™ | UHC™ |
| E ² CMOS™ | PowerTrench® | VCX™ |
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| FACT Quiet Series™ | QS™ | |
| FAST® | Quiet Series™ | |
| FASTr™ | SuperSOT™-3 | |
| GTO™ | SuperSOT™-6 | |

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